TO SEP. D TOP AND BOTTOM EDGES, SNAP—APART AN CARBON

FORM PTO-892 (REV. 3-78) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

NOTICE OF REFERENCES CITED

SERIAL NO.	GROUP ART UNIT	ATTACHMENT TO PAPER NUMBER
843454	114	2

APPLICANT(S): BLACHARD

U.S. PATENT DOCUMENTS

*		DOCUMENT NO.	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE
	A	4,582,565	4-86	KAWAKATSU	29	580	8-8-84
	B	4,509,249	4-85	GOTO ET AL.	29	576W	9-23-83
	C	4,374,455	2-83	GOODMAN	29	580	
	D	4,546,367	10-85	SCHUTTEN ET AL.	357	55	6-21-82
	E	4,596,999	6-86	GOBRECHT ET AL.	357	55	3-22-84
	F	4,345,265	8-82	BLACHARD	29	571	
	G						
	H						
	I						
	J						
	K						

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*		DOCUMENT NO.	DATE	COUNTRY	NAME	CLASS	SUB-CLASS	PERTINENT SHTS. DWG	PERTINENT PP. SPEC.
	L	0,065,447	4-84	JAPAN	KAZUYA	29	576W		
	M	0,108,325	6-84	JAPAN	TOSHIO	29	576W		
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	O								
	P								
	Q								

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EXAMINER	DATE
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*A copy of this reference is not being furnished with this office action.
(See Manual of Patent Examining Procedure, section 707.05 (a).)